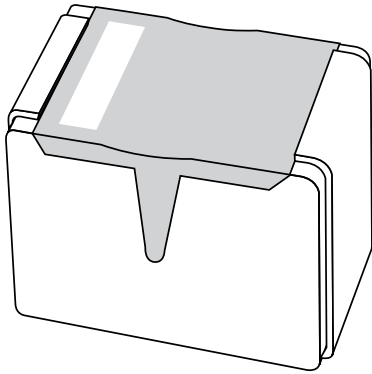


# DATA SHEET



**BAS216**

**High-speed switching diode**

Product specification  
Supersedes data of 1999 Apr 22

2002 May 28

# High-speed switching diode

# BAS216

## FEATURES

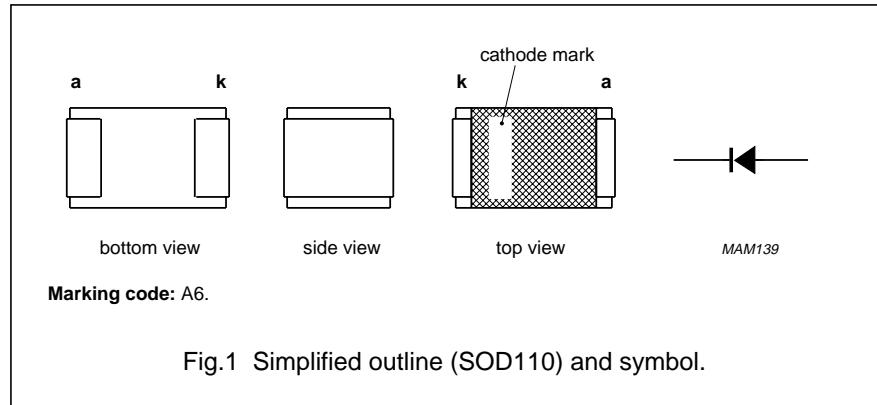
- Small ceramic SMD package
- High switching speed: max. 4 ns
- Continuous reverse voltage: max. 75 V
- Repetitive peak reverse voltage: max. 85 V
- Repetitive peak forward current: max. 500 mA.

## APPLICATIONS

- High-speed switching in e.g. surface mounted circuits.

## DESCRIPTION

The BAS216 is a high-speed switching diode fabricated in planar technology, and encapsulated in the SOD110 very small rectangular ceramic SMD package.



## LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
$V_{RRM}$	repetitive peak reverse voltage		–	85	V
$V_R$	continuous reverse voltage		–	75	V
$I_F$	continuous forward current	note 1	–	250	mA
$I_{FRM}$	repetitive peak forward current		–	500	mA
$I_{FSM}$	non-repetitive peak forward current	square wave; $T_j = 25\text{ °C}$ prior to surge; see Fig.4 $t = 1\ \mu\text{s}$ $t = 1\ \text{ms}$ $t = 1\ \text{s}$	–	4 1 0.5	A A A
$P_{tot}$	total power dissipation	$T_{amb} = 25\text{ °C}$ ; see Fig.2; note 1	–	400	mW
$T_{stg}$	storage temperature		–65	+150	°C
$T_j$	junction temperature		–	150	°C

## Note

1. Device mounted on an FR4 printed-circuit board.

## High-speed switching diode

## BAS216

**ELECTRICAL CHARACTERISTICS**

$T_j = 25\text{ °C}$  unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
$V_F$	forward voltage	see Fig.3			
		$I_F = 1\text{ mA}$	–	715	mV
		$I_F = 10\text{ mA}$	–	855	mV
		$I_F = 50\text{ mA}$	–	1	V
$I_R$	reverse current	see Fig.5			
		$V_R = 25\text{ V}$	–	30	nA
		$V_R = 75\text{ V}$	–	1	$\mu\text{A}$
		$V_R = 25\text{ V}; T_j = 150\text{ °C}$	–	30	$\mu\text{A}$
		$V_R = 75\text{ V}; T_j = 150\text{ °C}$	–	50	$\mu\text{A}$
$C_d$	diode capacitance	$f = 1\text{ MHz}; V_R = 0$ ; see Fig.6	–	1.5	pF
$t_{rr}$	reverse recovery time	when switched from $I_F = 10\text{ mA}$ to $I_R = 10\text{ mA}$ ; $R_L = 100\ \Omega$ ; measured at $I_R = 1\text{ mA}$ ; see Fig.7	–	4	ns
$V_{fr}$	forward recovery voltage	when switched from $I_F = 10\text{ mA}$ ; $t_r = 20\text{ ns}$ ; see Fig.8	–	1.75	V

**THERMAL CHARACTERISTICS**

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
$R_{th\ j-tp}$	thermal resistance from junction to tie-point		200	K/W
$R_{th\ j-a}$	thermal resistance from junction to ambient	note 1	315	K/W

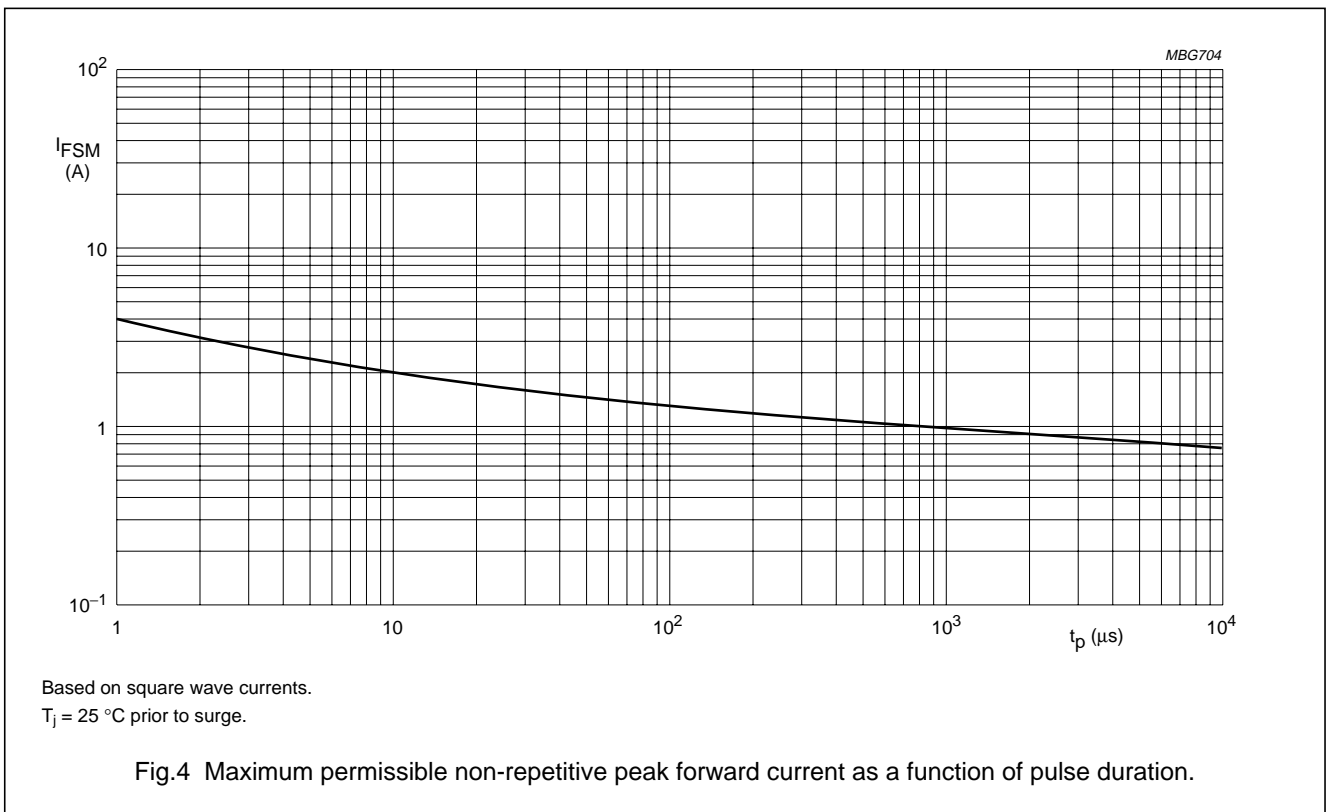
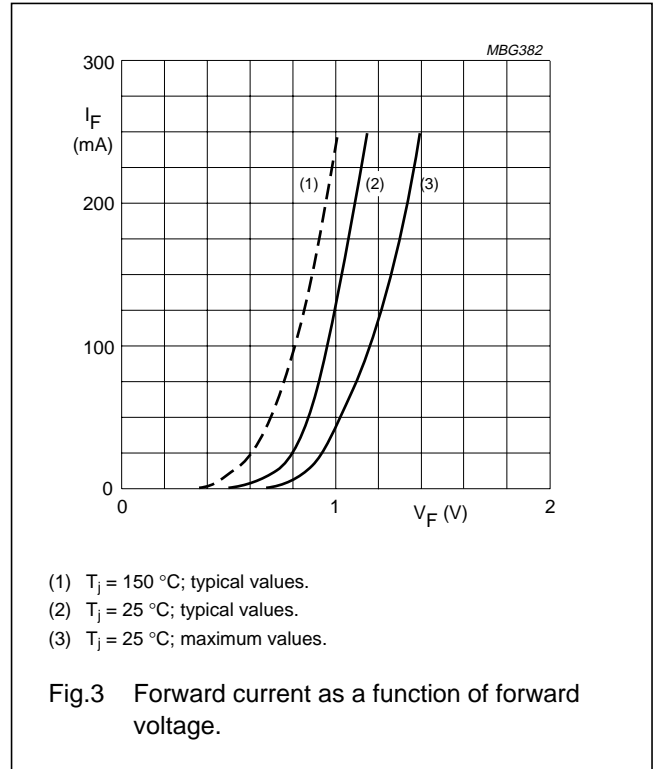
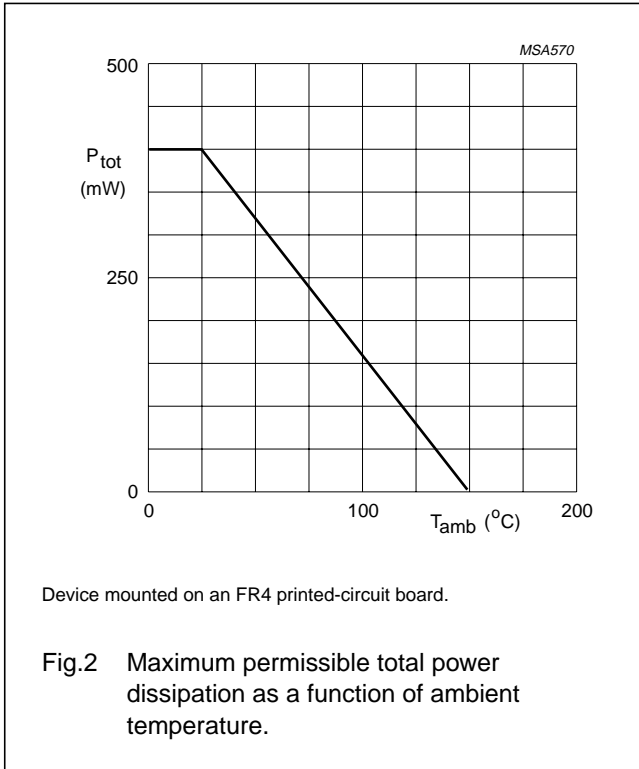
**Note**

1. Device mounted on an FR4 printed-circuit board.

High-speed switching diode

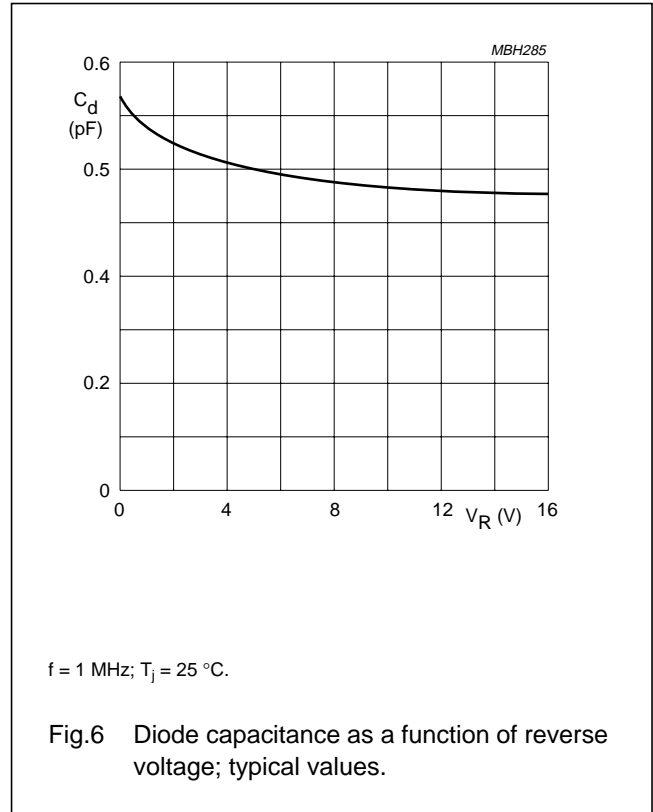
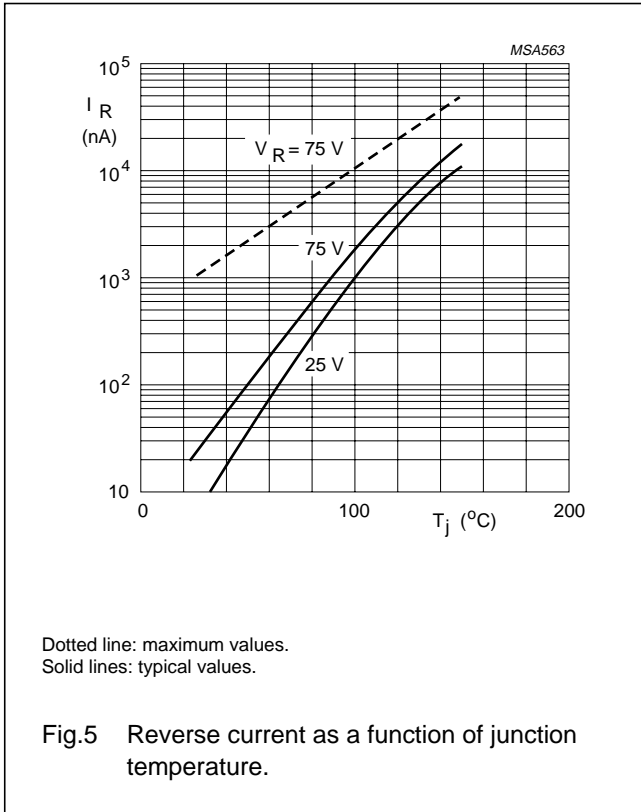
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GRAPHICAL DATA



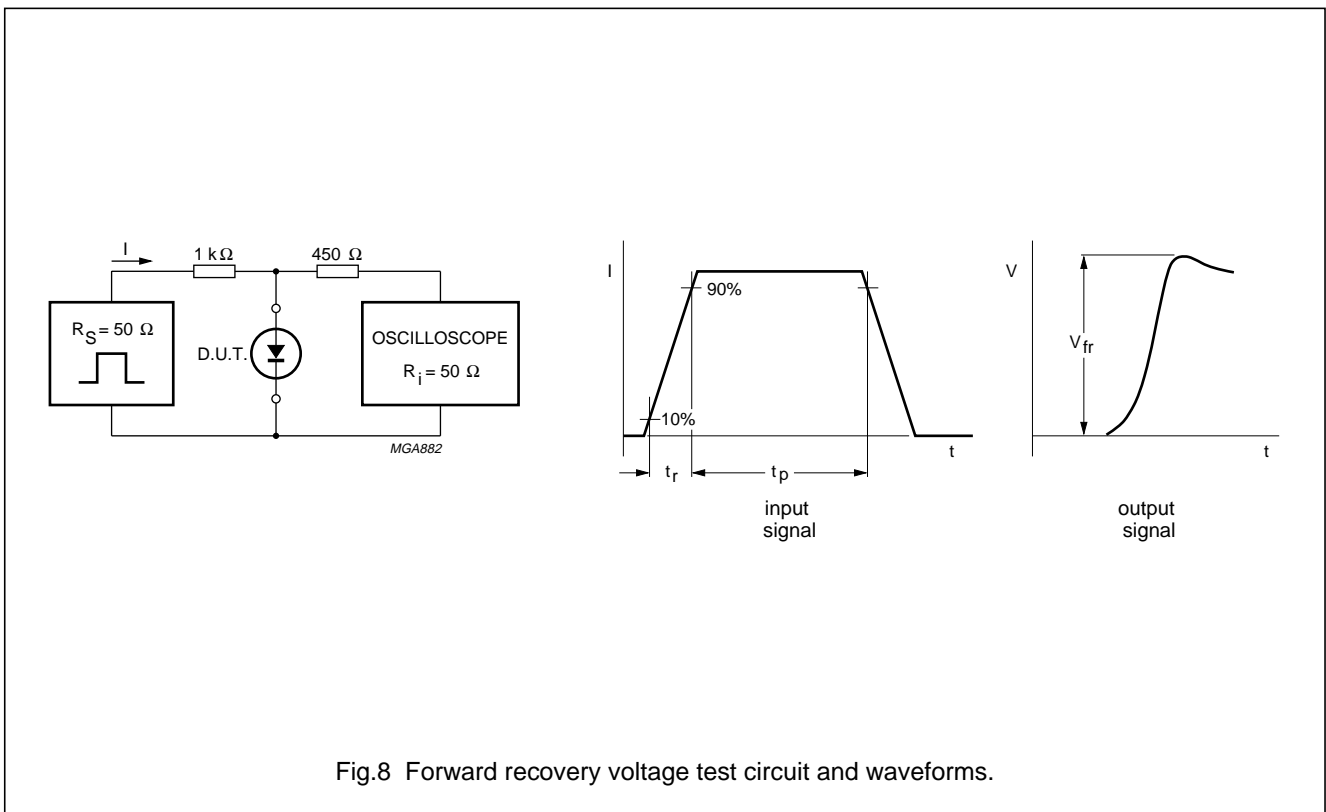
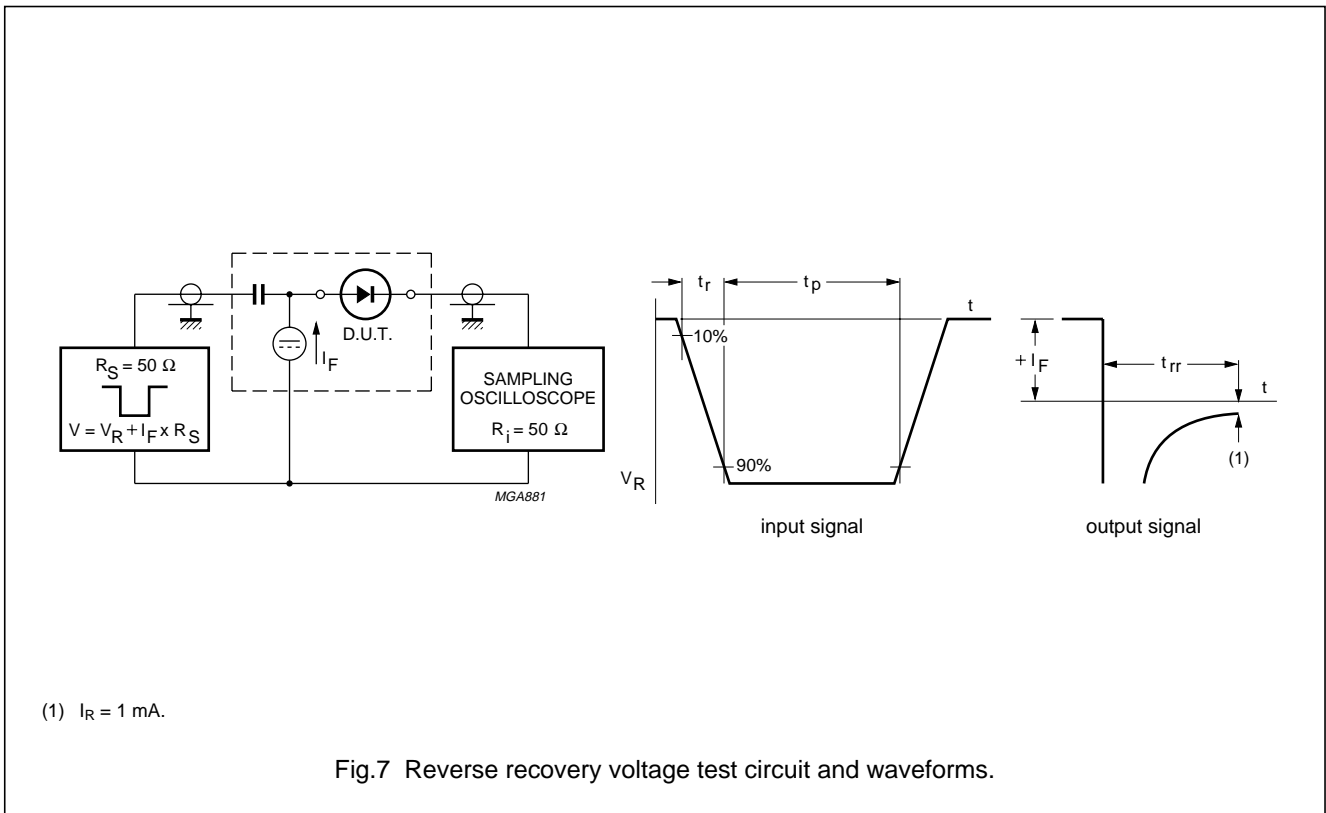
High-speed switching diode

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High-speed switching diode

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# High-speed switching diode

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## PACKAGE OUTLINE

Very small ceramic rectangular surface mounted package

SOD110

**DIMENSIONS (mm are the original dimensions)**

UNIT	A max.	D	E	y
mm	1.6	2.10 1.90	1.40 1.10	0.1

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	EIAJ			
SOD110						97-04-14

## High-speed switching diode

BAS216

## DATA SHEET STATUS

DATA SHEET STATUS <sup>(1)</sup>	PRODUCT STATUS <sup>(2)</sup>	DEFINITIONS
Objective data	Development	This data sheet contains data from the objective specification for product development. Philips Semiconductors reserves the right to change the specification in any manner without notice.
Preliminary data	Qualification	This data sheet contains data from the preliminary specification. Supplementary data will be published at a later date. Philips Semiconductors reserves the right to change the specification without notice, in order to improve the design and supply the best possible product.
Product data	Production	This data sheet contains data from the product specification. Philips Semiconductors reserves the right to make changes at any time in order to improve the design, manufacturing and supply. Changes will be communicated according to the Customer Product/Process Change Notification (CPCN) procedure SNW-SQ-650A.

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High-speed switching diode

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**NOTES**

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**NOTES**

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**NOTES**

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